

#### **Features**

- 1.2kV Schottky Rectifier
- Zero Reverse Recovery Current
- High-Frequency Operation
- Temperature-Independent Switching
- Extremely Fast Switching
- Positive Temperature Coefficient on V<sub>F</sub>

### **Benefits**

- Replace Bipolar with Unipolar Rectifiers
- Essentially No Switching Losses
- Higher Efficiency
- Reduction of Heat Sink Requirements
- Parallel Devices Without Thermal Runaway

#### **Applications**

- Switch Mode Power Supplies (SMPS)
- Boost diodes in PFC or DC/DC stages
- Free Wheeling Diodes in Inverter stages
- AC/DC converters



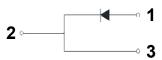


Part Number	Package	Qty(PCS)
HMSC020SDA120K	TO-220H-2L	50

## **Maximum Ratings** (T<sub>c</sub>=25°C unless otherwise specified)

Symbol	Parameter	Value	Unit	Test Conditions	Note
V <sub>RRM</sub>	Repetitive Peak Reverse Voltage	1200	V		
V <sub>RSM</sub>	Surge Peak Reverse Voltage	1300	٧		
V <sub>R</sub>	DC Peak Reverse Voltage	1200	V		
I <sub>F</sub>	Continuous Forward Current	54.5 26 20	А	T <sub>c</sub> =25°C T <sub>c</sub> =135°C T <sub>c</sub> =150°C	Fig. 3
I <sub>FRM</sub>	Repetitive Peak Forward Surge Current	91 61	А	T <sub>c</sub> =25°C, t <sub>p</sub> =10 ms, Half Sine Pulse T <sub>c</sub> =110°C, t <sub>p</sub> =10 ms, Half Sine Pulse	
I <sub>FSM</sub>	Non-Repetitive Forward Surge Current	130 110	А	T <sub>c</sub> =25°C, t <sub>p</sub> =10 ms, Half Sine Pulse T <sub>c</sub> =110°C, t <sub>p</sub> =10 ms, Half Sine Pulse	Fig. 8
I <sub>F,Max</sub>	Non-Repetitive Peak Forward Current	1150 950	Α	$T_c$ =25°C, $t_p$ =10 ms, Pulse $T_c$ =110°C, $t_p$ =10 ms, Pulse	Fig. 8
P <sub>tot</sub>	Power Dissipation	250 112.5	W	T <sub>c</sub> =25°C T <sub>c</sub> =110°C	Fig. 4
dV/dt	Diode dV/dt ruggedness	200	V/ns	V <sub>R</sub> =0-960V	
∫i²dt	i²t value	84.5 60.5	A²s	$T_c$ =25°C, $t_p$ =10 ms $T_c$ =110°C, $t_p$ =10 ms	
T <sub>J</sub>	Operating Junction Range	-55 to +175	°C		
T <sub>stg</sub>	Storage Temperature Range	-55 to +135	°C		
	TO-220 Mounting Torque	1 8.8	Nm lbf-in	M3 Screw 6-32 Screw	







### **Electrical Characteristics**

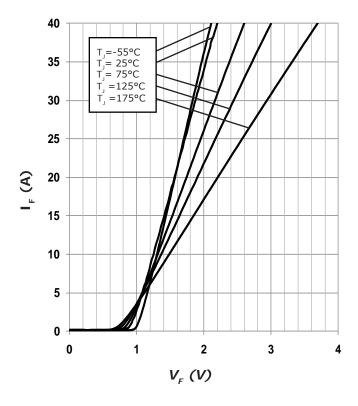
Symbol	Parameter	Тур.	Max.	Unit	Test Conditions	Note
V <sub>F</sub>	Forward Voltage	1.5 2.2	1.8 3	V	I <sub>F</sub> = 20 A T <sub>J</sub> =25°C I <sub>F</sub> = 20 A T <sub>J</sub> =175°C	Fig. 1
I <sub>R</sub>	Reverse Current	35 65	200 400	μΑ	V <sub>R</sub> = 1200 V T <sub>J</sub> =25°C V <sub>R</sub> = 1200 V T <sub>J</sub> =175°C	Fig. 2
Q <sub>c</sub>	Total Capacitive Charge	99		nC	$V_R = 800 \text{ V, } I_F = 20\text{A}$ $di/dt = 200 \text{ A/}\mu\text{s}$ $T_J = 25^{\circ}\text{C}$	Fig. 5
С	Total Capacitance	1500 93 67		pF	V <sub>R</sub> = 0 V, T <sub>J</sub> = 25°C, f = 1 MHz V <sub>R</sub> = 400 V, T <sub>J</sub> = 25°C, f = 1 MHz V <sub>R</sub> = 800 V, T <sub>J</sub> = 25°C, f = 1 MHz	Fig. 6
E <sub>c</sub>	Capacitance Stored Energy	28		μЈ	V <sub>R</sub> = 800 V	Fig. 7

Note: This is a majority carrier diode, so there is no reverse recovery charge.

### **Thermal Characteristics**

Symbol	Parameter	Тур.	Unit	Note
$R_{\theta JC}$	Thermal Resistance from Junction to Case	0.6	°C/W	Fig. 9

## **Typical Performance**





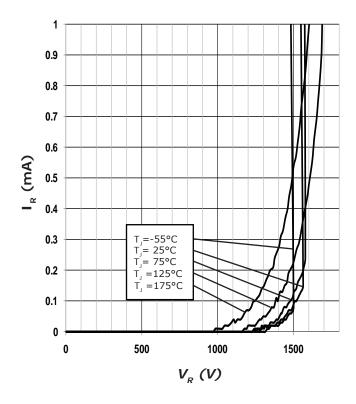


Figure 2. Reverse Characteristics



## **Typical Performance**

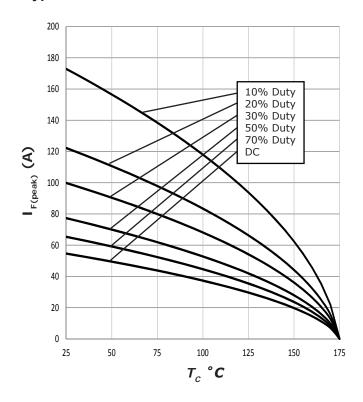


Figure 3. Current Derating

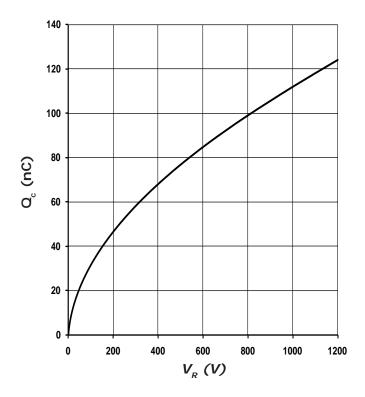


Figure 5. Recovery Charge vs. Reverse Voltage

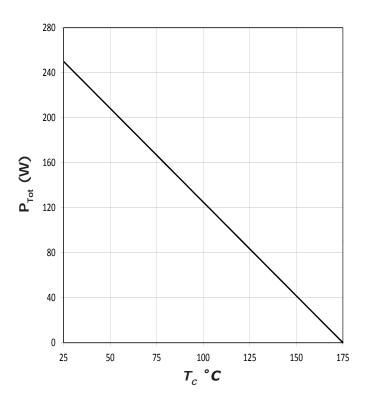


Figure 4. Power Derating

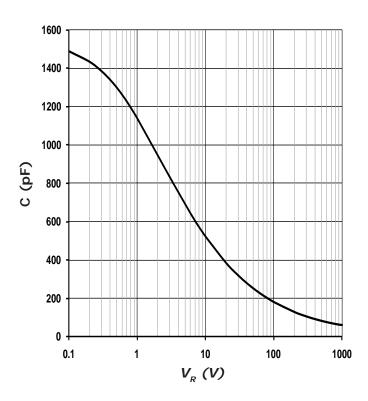
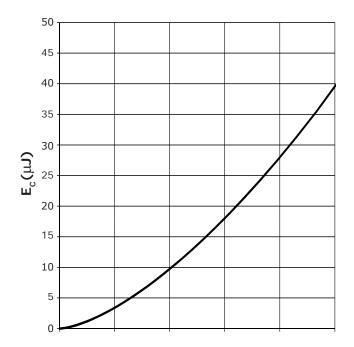


Figure 6. Capacitance vs. Reverse Voltage



## **Typical Performance**



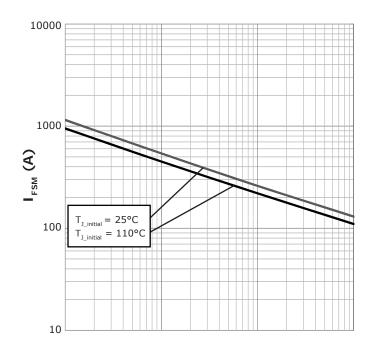


Figure 7. Typical Capacitance Stored Energy

Figure 8. Non-Repetitive Peak Forward Surge Current versus Pulse Duration (sinusoidal waveform)

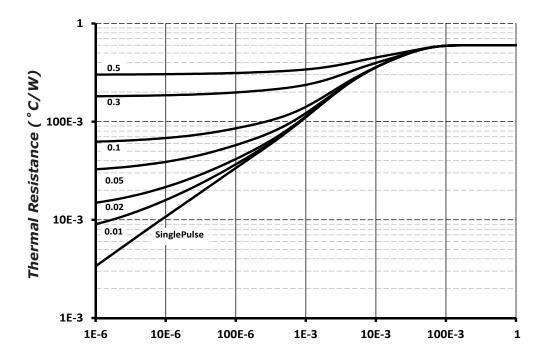
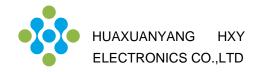


Figure 9. Transient Thermal Impedance *T (Sec)* 



## **Diode Model**

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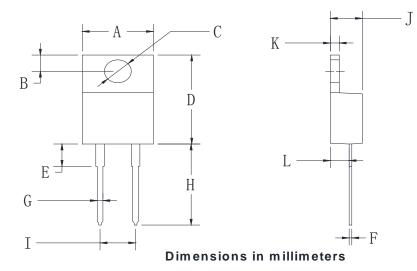
$$V_{fT} = V_T + If^*R_T$$

$$V_T = 0.97 + (T_J^* - 1.40^* 10^{-3})$$
  
 $R_T = 0.023 + (T_J^* 2.71^* 10^{-4})$ 

Note: T<sub>j</sub> = Diode Junction Temperature In Degrees Celsius, valid from 25°C to 175°C

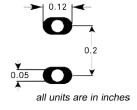


# Package Information TO-220H-2L



TO-220H-2L				
Dim	Min	Max		
Α	9.5	10.9		
В	2.22	3.27		
С	3.34	4.31		
D	14.5	15.5		
Е	3.16	4.46		
F	0.28	0.64		
G	0.68	0.94		
Н	13.06	14.62		
I	4.55	5.60		
J	4.04	5.1		
K	1.14	1.4		
L	2.14	3.19		

# **Recommended Solder Pad Layout**



TO-220H2L

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